

RJL5012DPP

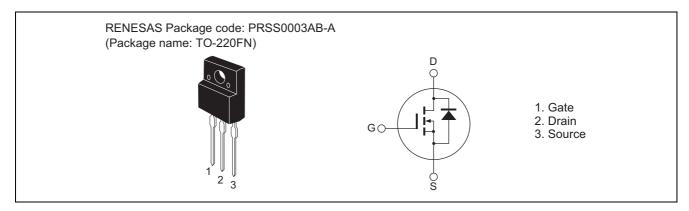
Silicon N Channel MOS FET High Speed Power Switching

REJ03G1746-0200 Rev.2.00 Mar 05, 2009

Features

- Built-in fast recovery diode
- Low on-resistance
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

| Item | Symbol | Ratings | Unit |
|---|------------------------------|-------------|------|
| Drain to source voltage | V_{DSS} | 500 | V |
| Gate to source voltage | V_{GSS} | ±30 | V |
| Drain current | I _D Note4 | 12 | Α |
| Drain peak current | I _{D (pulse)} Note1 | 36 | А |
| Body-drain diode reverse drain current | I _{DR} | 12 | А |
| Body-drain diode reverse drain peak current | Note1 DR (pulse) | 36 | А |
| Avalanche current | I _{AP} Note3 | 3 | А |
| Avalanche energy | E _{AR} Note3 | 0.5 | mJ |
| Channel dissipation | Pch Note2 | 30 | W |
| Channel to case thermal impedance | θch-c | 4.17 | °C/W |
| Channel temperature | Tch | 150 | °C |
| Storage temperature | Tstg | -55 to +150 | °C |

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

- 2. Value at Tc = 25°C
- 3. STch = 25° C, Tch $\leq 150^{\circ}$ C
- 4. Limited by maximum safe operation area

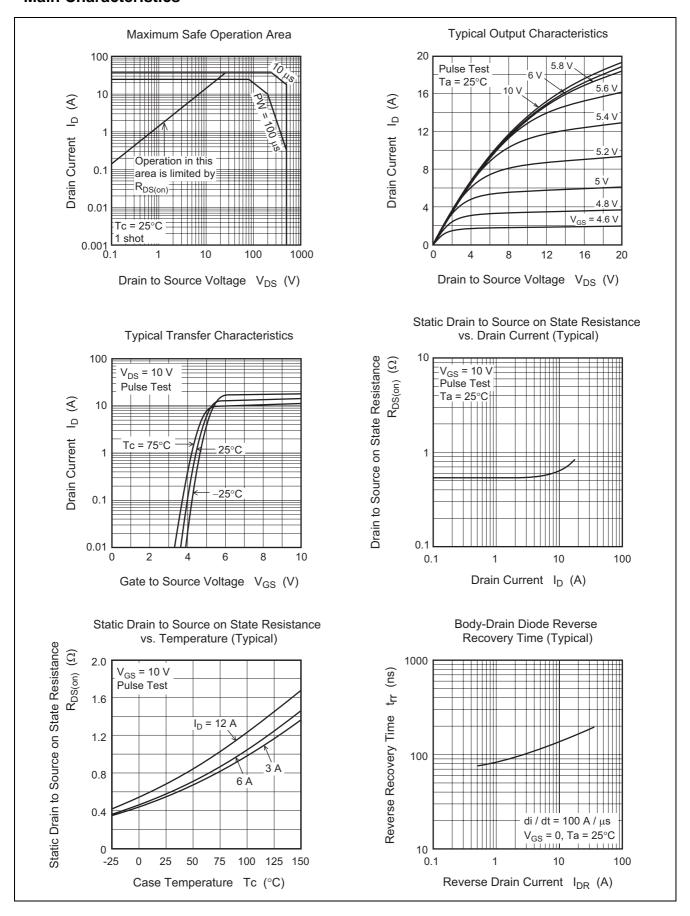
Electrical Characteristics

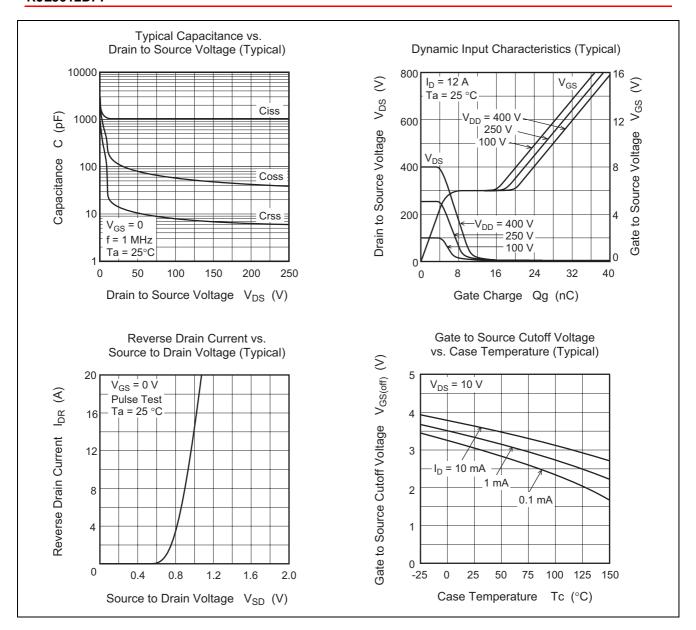
 $(Ta = 25^{\circ}C)$

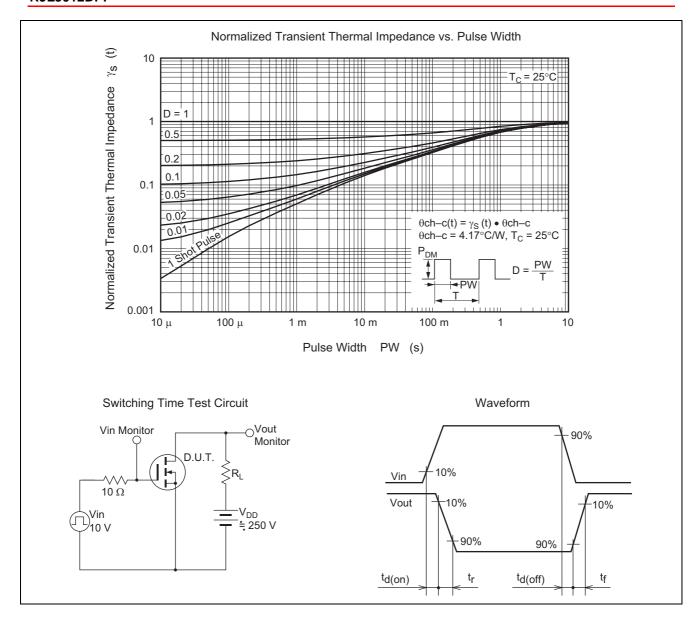
| Item | Symbol | Min | Тур | Max | Unit | Test conditions |
|--|---------------------|-----|------|------|------|---|
| Drain to source breakdown voltage | $V_{(BR)DSS}$ | 500 | _ | _ | V | $I_D = 10 \text{ mA}, V_{GS} = 0$ |
| Zero gate voltage drain current | I _{DSS} | _ | _ | 10 | μΑ | $V_{DS} = 500 \text{ V}, V_{GS} = 0$ |
| Gate to source leak current | I _{GSS} | _ | _ | ±0.1 | μΑ | $V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$ |
| Gate to source cutoff voltage | $V_{GS(off)}$ | 2.0 | _ | 4.0 | V | $V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$ |
| Static drain to source on state resistance | R _{DS(on)} | _ | 0.56 | 0.70 | Ω | $I_D = 6 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note5}}$ |
| Input capacitance | Ciss | _ | 1050 | _ | pF | V _{DS} = 25 V |
| Output capacitance | Coss | _ | 115 | _ | pF | V _{GS} = 0 f = 1 MHz |
| Reverse transfer capacitance | Crss | _ | 14 | _ | pF | |
| Turn-on delay time | t _{d(on)} | _ | 27 | _ | ns | $I_D=6~A$ $V_{GS}=10~V$ $R_L=41.7~\Omega$ $Rg=10~\Omega$ |
| Rise time | t _r | _ | 22 | _ | ns | |
| Turn-off delay time | $t_{d(off)}$ | _ | 78 | _ | ns | |
| Fall time | t _f | _ | 15 | _ | ns | |
| Total gate charge | Qg | _ | 27.8 | _ | nC | V _{DD} = 400 V |
| Gate to source charge | Qgs | _ | 4.9 | _ | nC | V _{GS} = 10 V I _D = 12 A |
| Gate to drain charge | Qgd | _ | 14.4 | _ | nC | |
| Body-drain diode forward voltage | V_{DF} | _ | 0.96 | 1.60 | V | I _F = 12 A, V _{GS} = 0 Note5 |
| Body-drain diode reverse recovery time | t _{rr} | _ | 140 | _ | ns | $I_F = 12 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$ |

Notes: 5. Pulse test

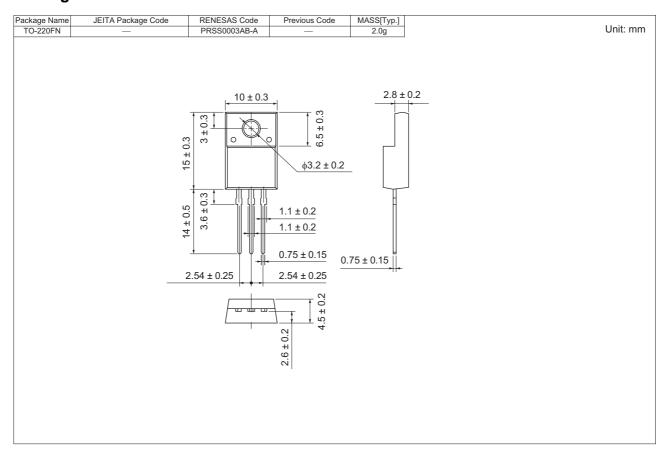
Main Characteristics







Package Dimensions



Ordering Information

| Part No. | Quantity | Shipping Container |
|------------------|----------|--------------------|
| RJL5012DPP-00-T2 | 1050 pcs | Box (Tube) |

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